MSKSEMI美森科













ESD

TVS

TSS

MOV

GDT

PLED

MMSD914

Product specification

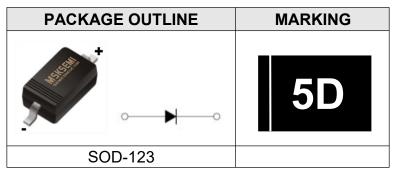




FEATURES

High Voltage

Reference News



MAXIMUM RATINGS (Ta=25 $^\circ\!\!\mathbb{C}$ unless otherwise noted)

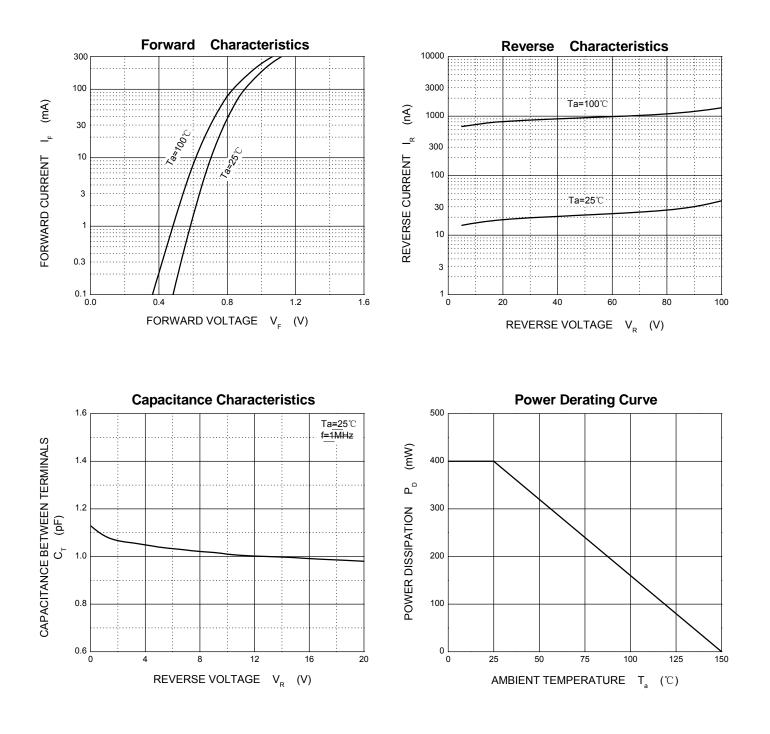
Symbol	Parameter	Value	Unit	
V _{RRM}	Maximum Repetitive Reverse Voltage	100	V	
lo	Forward Current	0.2	А	
IFSM	Non-repetitive Peak Forward Surge Current @t= 8.3ms 2			
PD	Power Dissipation	400	mW	
R _{0JA}	Thermal Resistance from Junction to Ambient	312	°C/W	
Tj ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C	

ELECTRICAL CHARACTERISTICS(Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Reverse voltage	V _(BR)	l _R =100µA	100			V
Reverse current	lĸ	V _R =20V			25	nA
		V _R =75V			5	μA
Forward voltage	VF	l⊧=10mA			1	V
Total capacitance	Ctot	V _R =0V,f=1MHz			4	pF
Reverse recovery time	t _{rr}	I⊧= I _R =10mA, I _{rr} =0.1×I _R , R∟=100Ω			4	ns

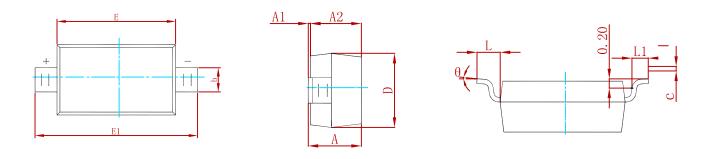






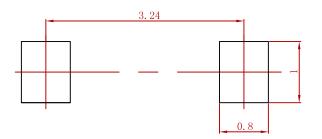


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
А	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.450	0.650	0.018	0.026	
С	0.080	0.150	0.003	0.006	
D	1.500	1.700	0.059	0.067	
E	2.600	2.800	0.102	0.110	
E1	3.550	3.850	0.140	0.152	
L	0.500 REF		0.020 REF		
L1	0.250	0.450	0.010	0.018	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

1.Controllng dlmenslon:in mlllmeters. 2.General tolerance:± 0.05mm.

3. The pad layout Is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MMSD914	SOD-123	3000



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